

chain nodes :

10 11 12 13 14

ring nodes :

1 2 3 4 5 6 7 8 9

chain bonds :

7-11 8-12 9-10 12-13 12-14

ring bonds :

1-3 1-2 2-6 3-4 4-5 5-6 5-7 6-9 7-8 8-9

exact/norm bonds :

7-11 8-12 9-10 12-13 12-14

exact bonds :

1-3 1-2 2-6 3-4 4-5 5-6 5-7 6-9 7-8 8-9

Match level :

1:Atom 2:Atom 3:Atom 4:Atom 5:Atom 6:Atom 7:Atom 8:Atom 9:Atom 10:CLASS 11:CLASS
12:CLASS 13:CLASS 14:CLASS

ENTER SCREEN EXPRESSION OR (END) :end

=> screen 2067

L1 SCREEN CREATED

=>
Uploading C:\Program Files\Stnexp\Queries\095p.str

L2 STRUCTURE UPLOADED

=> que L2 AND L1

L3 QUE L2 AND L1

=> s l3 full
FULL SEARCH INITIATED 18:51:02 FILE 'REGISTRY'
FULL SCREEN SEARCH COMPLETED - 5 TO ITERATE

100.0% PROCESSED 5 ITERATIONS
SEARCH TIME: 00.00.01

1 ANSWERS

L4 1 SEA SSS FUL L2 AND L1

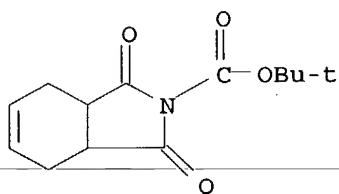
=> d

L4 ANSWER 1 OF 1 REGISTRY COPYRIGHT 2004 ACS on STN
RN 488722-50-5 REGISTRY
CN 2H-Isoindole-2-carboxylic acid, 1,3,3a,4,7,7a-hexahydro-1,3-dioxo-,
1,1-dimethylethyl ester, polymer with 3,3,4,4,5,5,6,6,6-nonafluoro-1-
hexene and 3a,4,7,7a-tetrahydro-1H-isoindole-1,3(2H)-dione (9CI) (CA
INDEX NAME)
MF (C13 H17 N O4 . C8 H9 N O2 . C6 H3 F9)x
CI PMS
PCT Polyether, Polyvinyl
SR CA
LC STN Files: CA, CAPLUS, USPATFULL

CM 1

CRN 488722-49-2

CMF C13 H17 N O4



CM 2

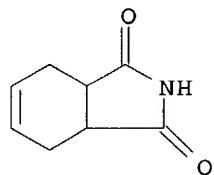
CRN 19430-93-4

CMF C6 H3 F9

H₂C=CH-(CF₂)₃-CF₃

CM 3

CRN 85-40-5
CMF C8 H9 N O2



1 REFERENCES IN FILE CA (1907 TO DATE)
1 REFERENCES IN FILE CAPLUS (1907 TO DATE)

=>

=> d bib ab hitstr

L5 ANSWER 1 OF 1 CAPLUS COPYRIGHT 2004 ACS on STN
AN 2003:58673 CAPLUS
DN 138:115067

TI Chemical amplification photoresist monomers, polymers therefrom and
photoresist compositions containing the same

IN Jung, Jae Chang; Lee, Geun Su; Shin, Ki Soo

PA S. Korea

SO U.S. Pat. Appl. Publ., 8 pp.

CODEN: USXXCO

DT Patent

LA English

FAN.CNT 1

	PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
PI	US 2003017404	A1	20030123	US 2002-54095	20020122
PRAI	KR 2001-38030	A	20010629		
OS	MARPAT 138:115067				

AB The present invention relates to a chem. amplification photoresist monomer, a photoresist polymer prep'd. from it, and a photoresist compn. using the polymer. More specifically, a chem. amplification photoresist polymer comprises a fluorine-contg. monomer R1R3C=CR2R4 (R1-4 = H, halogen-substituted alkyl). The photoresist compn. has excellent etching resistance, heat resistance and adhesiveness, and is developable in aq. tetramethylammonium hydroxide (TMAH) soln. As the compn. has low light absorbance at 193 nm and 157 nm wavelength, it is very useful for forming ultramicro pattern in the process using a light source of far UV, esp. of VUV (157 nm).

IT 488722-50-5P

RL: PRP (Properties); SPN (Synthetic preparation); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses)
(chem. amplification photoresist monomers, polymers for photoresist compns.)

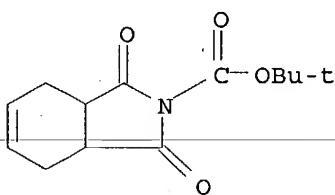
RN 488722-50-5 CAPLUS

CN 2H-Isoindole-2-carboxylic acid, 1,3,3a,4,7,7a-hexahydro-1,3-dioxo-,
1,1-dimethylethyl ester, polymer with 3,3,4,4,5,5,6,6,6-nonafluoro-1-
hexene and 3a,4,7,7a-tetrahydro-1H-isoindole-1,3(2H)-dione (9CI) (CA
INDEX NAME)

CM 1

CRN 488722-49-2

CMF C13 H17 N O4



CM 2

CRN 19430-93-4

CMF C6 H3 F9

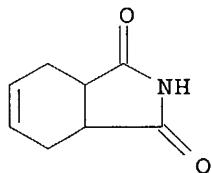
H₂C=CH-(CF₂)₃-CF₃

$\text{H}_2\text{C}=\text{CH}- (\text{CF}_2)_3-\text{CF}_3$

CM 3

CRN 85-40-5

CMF C8 H9 N O2



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